



Durability of Thin Film Solar Cells

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Empa, Dübendorf

Outdoor measurements and comparison of thin film solar cell technologies

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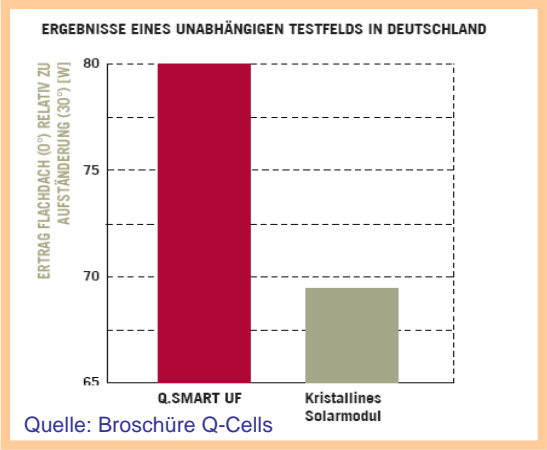
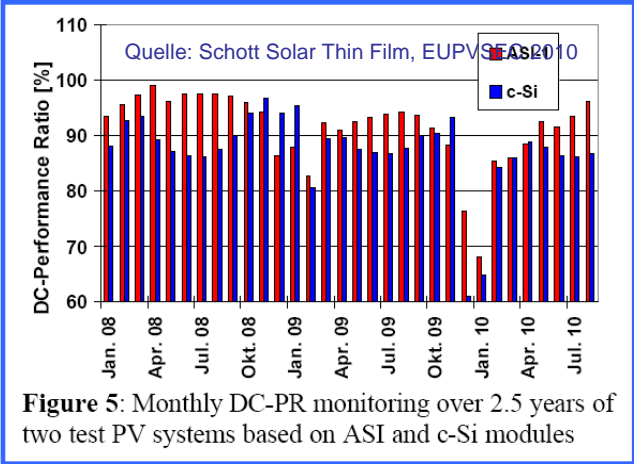
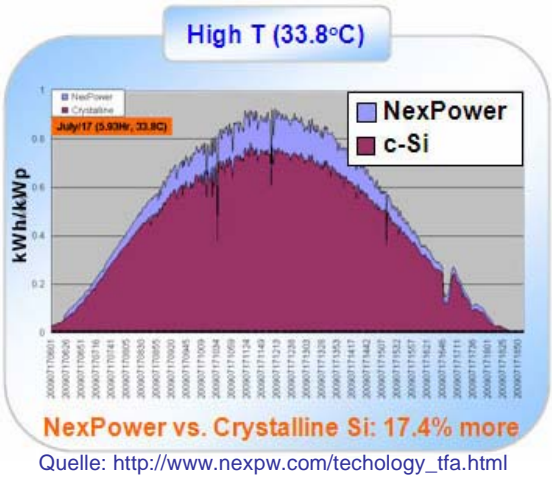
Motivation

Higher uncertainties of module parameters for thin film technologies (CIGS, CdTe, a-Si/ μ -Si) compared to c-Si.

Operational parameters, energy yield and long term stability can be determined from outdoor measurements.



More energy from thin film PV – Marketing or reality?



More energy from thin film PV in principle possible by:

- lower temperature coefficient
- good performance under low/diffuse light
- annealing or light-soaking effects



Information from data sheet

ELEKTRISCHE SPEZIFIKATIONEN

Daten gemessen unter Standard-Testbedingungen (STC)*:

PowerMax® STRONG	110	115	120	125	130	135
Nominalleistung P_{nom}	110 W	115 W	120 W	125 W	130 W	135 W
Toleranz der Nominalleistung ΔP_{nom}	-0/+5 %	-0/+5 %	-0/+5 %	-0/+4 %	-0/+4 %	-0/+4 %
Modul-Wirkungsgrad η^{**}	10,3 %	10,7 %	11,2 %	11,7 %	12,1 %	12,6 %
Apertur-Wirkungsgrad η	11,6 %	12,2 %	12,7 %	13,2 %	13,7 %	14,2 %
Leerlaufspannung V_{oc}	56,9 V	57,7 V	58,5 V	59,3 V	60,2 V	61,1 V
Kurzschlussstrom I_{sc}	3,19 A	3,20 A	3,21 A	3,22 A	3,23 A	3,24 A
Spannung im mpp V_{mpp}	40,4 V	41,6 V	42,8 V	44,0 V	45,3 V	46,6 V
Stromstärke im mpp I_{mpp}	2,72 A	2,76 A	2,80 A	2,84 A	2,87 A	2,90 A
Rückstrombelastbarkeit I_r	5,0 A	5,0 A	5,0 A	5,0 A	5,0 A	5,0 A
Max. Systemspannung V_{sys} (IEC)	1000 V	1000 V	1000 V	1000 V	1000 V	1000 V
Max. Systemspannung V_{sys} (UL)	600 V	600 V	600 V	600 V	600 V	600 V

* Bestrahlungsstärke 1000 W/m² in der Modulebene, Modultemperatur 25 °C und eine Spektralverteilung der Bestrahlung gemäß der atmosphärischen Masse (AM) 1,5.
** Ausschl. Montagerand.

Daten gemessen bei Zellen-Nennbetriebstemperatur (NOCT)* und AM 1,5:

PowerMax® STRONG	110	115	120	125	130	135
NOCT	40,0 °C	40,0 °C	40,0 °C	40,0 °C	40,0 °C	40,0 °C
Nominalleistung P_{nom}	82,0 W	85,8 W	89,5 W	93,2 W	96,9 W	100,7 W
Leerlaufspannung V_{oc}	53,3 V	54,0 V	54,8 V	55,6 V	56,5 V	57,4 V
Kurzschlussstrom I_{sc}	2,51 A	2,51 A	2,51 A	2,51 A	2,51 A	2,51 A
Spannung im mpp V_{mpp}	37,5 V	38,7 V	39,9 V	41,1 V	42,3 V	43,6 V

* NOCT: Modultemperatur bei 800 W/m² Bestrahlungsstärke in der Modulebene, Lufttemperatur 20 °C, Windgeschwindigkeit 1 m/s und Leerlaufzustand.

Temperatur-Koeffizienten:

PowerMax® STRONG	Wert
Temperatur-Koeffizient P_{nom}	-0,39 %/°C
Temperatur-Koeffizient V_{oc}	-170 mV/°C
Temperatur-Koeffizient I_{sc}	0,10 mA/°C
Temperatur-Koeffizient V_{mpp}	-140 mV/°C

Daten gemessen bei geringer Strahlungsintensität:
Die relative Verringerung des Modulwirkungsgrads bei einer Strahlungsintensität von 200 W/m², bezogen auf 1000 W/m² bei 25 °C Modultemperatur und Spektrum AM 1,5, beträgt 10 %. Bei 500 W/m² beträgt die relative Verringerung des Modulwirkungsgrads 1 %.

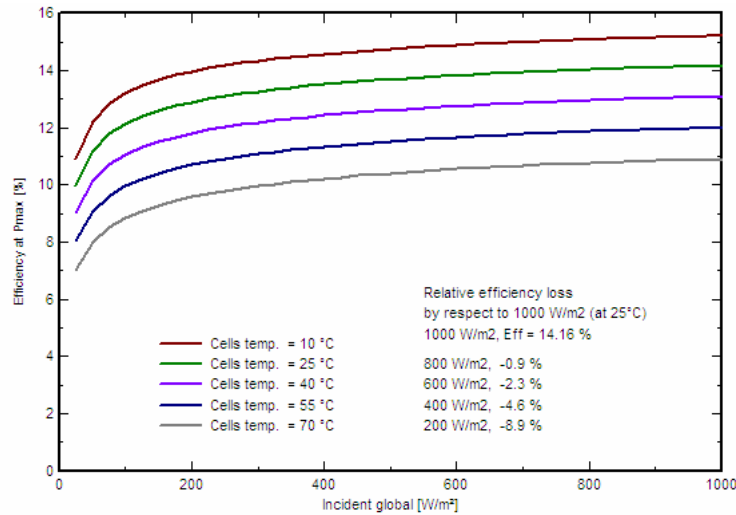
- STC power/tolerance

- Temperature coeff.

- Dependence on irradiance

Source: http://www.avancis.de/fileadmin/media/portal/produkt/Datenblatt_PowerMax-STRONG.pdf

Information from simulation programs



Nom. Power (at STC) **245** Wp Tol. **0.1** % Technology **Si-mono**

Manufacturer specifications or other Measurements

Reference conditions: GRef **1000** W/m² TRef **25** °C
 Short-circuit current Isc **8.900** A Open circuit Voc **36.80** V
 Max Power Point: Impp **8.220** A Vmpp **29.80** V
 Temperature coefficient: mulsc **2.7** mA/°C Nb cells **60 in series**
 or mulsc **0.03** %/°C

Internal model result tool

Operating conditions: GOper **1000** W/m² TOper **25** °C
 Max Power Point: Pmpp **245.0** W Temper. coeff. **-0.50** %/°C
 Current Impp **8.20** A Voltage Vmpp **29.9** V
 Short-circuit current Isc **8.90** A Open circuit Voc **36.8** V
 Efficiency / Cells area **N/A** % / Module area **14.73** %

Model summary

Main parameter

R shunt **220 ohm**
 Rsh(G=0) **900 ohm**

R serie model **0.18 ohm**
 R serie max. **0.40 ohm**
 R serie apparent **0.40 ohm**

Model parameters

Gamma **1.30**
 IoRef **92 nA**
 muVoc **-146 mV/°C**
 muPMMax fixed **-0.50 /°C**

Source: PVSYS

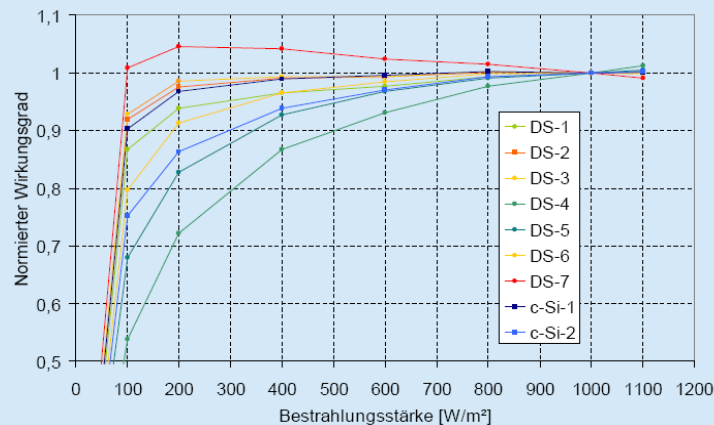
Data for

- STC power/efficiency
- Temperature coefficients
- Dependence on irradiance

Where are these data from??

Information from simulator measurements

Schwachlichtverhalten von Dünnschicht-Modulen
Wirkungsgrad (bei 25°C und AM 1,5)



Quelle: TÜV Rheinland

Measurement according to IEC 61853

(PV Module Performance Testing and Energy Rating):

- Irradiance 100, 200, 400, 600, 800, 1000, 1100 W/m²
- Temperature 15, 25, 50, 75 °C

Restrictions for thin film flasher measurements:

- Metastability effects
- Crystalline Si reference cells
- Current mismatch for tandem cells
- Transient effects

Results from outdoor module characterization

- STC power:
 - data collection days to weeks
 - spectrum dependent on location and season
 - stability presupposed
- Energy generation, Performance Ratio (PR):
 - typically 1 year
 - comparison of different technologies (benchmark c-Si)
 - valid for selected site
- Parameter determination:
 - typically 1 year
 - power, Voc, Isc,.. under STC
 - temperature coefficients, operation temperature
 - dependence on irradiance, incidence angle, spectrum
- Long term stability
 - several years

Energy and Performance Ratio

- Energy Yield:

$$Y = E_{\text{counter}} / P_{\text{nom}} \quad (\text{kWh/kWp})$$

- Performance Ratio (PR)

$$\text{PR} = Y / E_{\text{POA}} \quad (\%)$$

- Which P_{nom} ? Label? Flasher or outdoor measurement?
- Measured irradiation in module plane (E_{POA}) depends on sensor

Outdoor measurements at ZSW

- **Widderstall (since 1988)**
- **Girona/Spain (since 2011)**

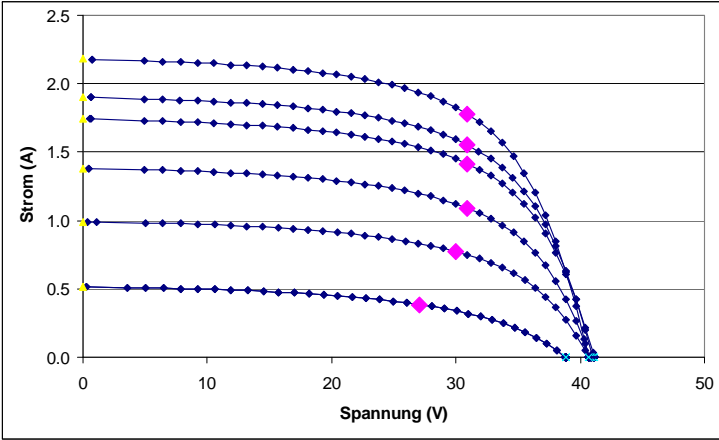
- **Module measurements**
 - module kept at MPP
 - I-V characteristics (1 per minute)
 - T_{mod}
 - Pyranometer and c-Si ref. cell
 - T_a, GHI, DHI, DNI, TNI, v_{wind}

- **Generator measurements**
 - 1kW, identical inverters
 - DC, AC voltage and current
 - T_{mod}, POA irradiance

- **PID-test stand**



Outdoor measurements at ZSW

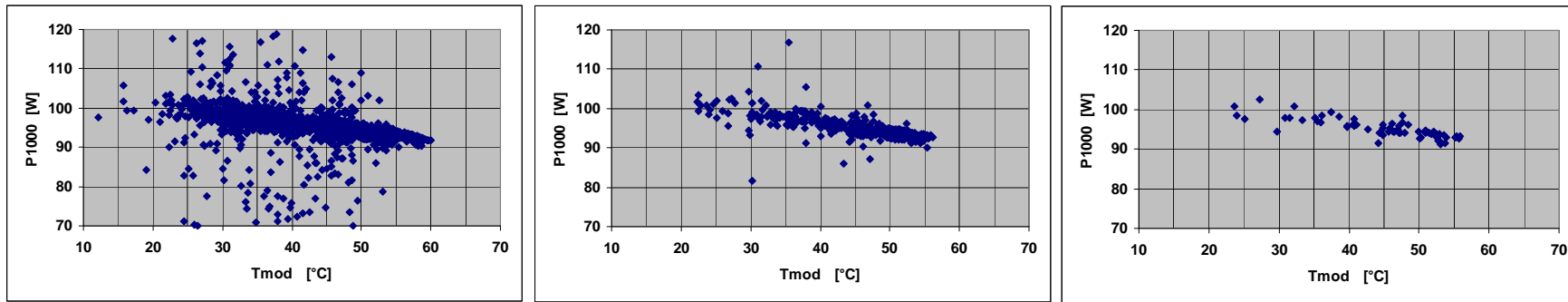


Module I-V characteristics



Power and temperature coefficient: (1) Selection of irradiance interval

Calculation of P1000 (linear scaling with reference irradiance)



Data collection September, Widderstall, Si-TF module

1000 W/m² +/- 10%
2854 Data points

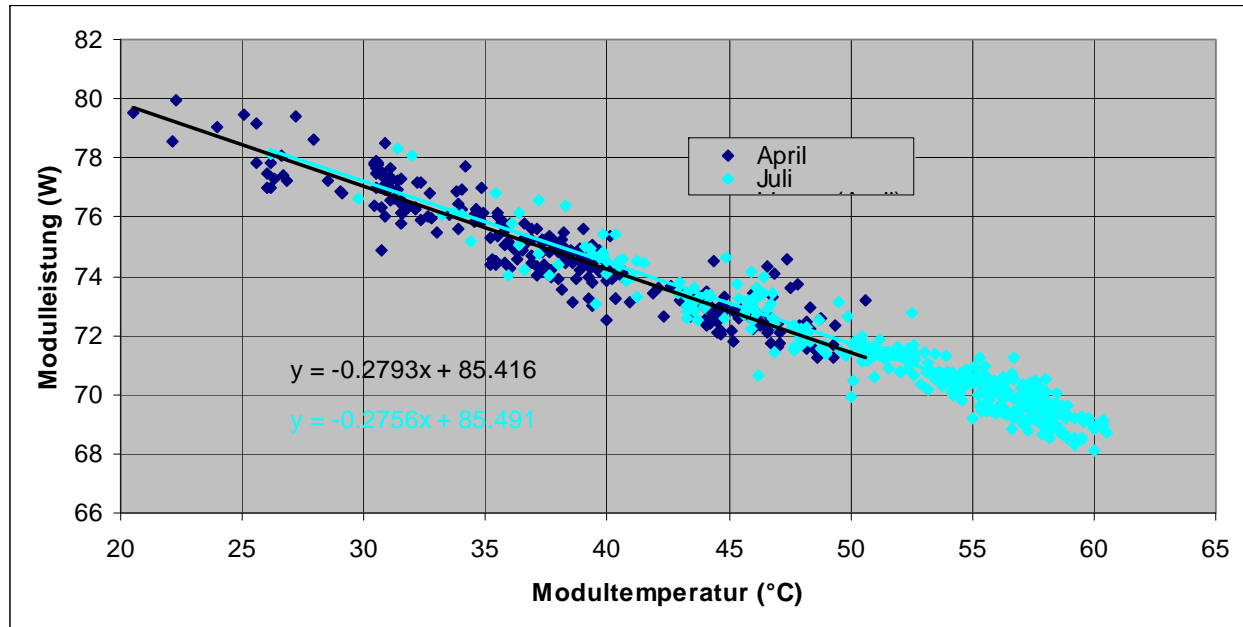
1000 W/m² +/- 2%
492 Data points

1000 W/m² +/- 0,2%
74 Data points

Reasonable range:

- Irradiance interval +/-1 to 2 %
- some 100 to 1000 data points

Power and temperature coefficient: (2) Different measurement periods



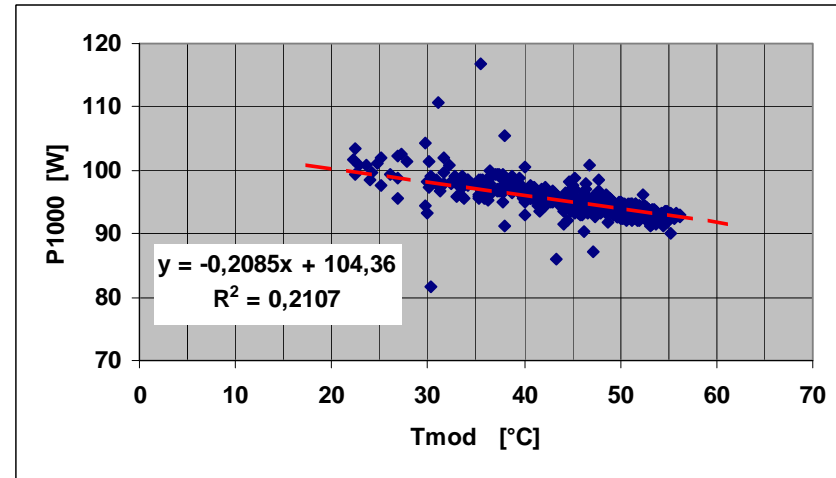
Measurement months April and July, Widderstall, CIGS module

- Higher module temperature in July
- No change of STC module power

Power and temperature coefficient: (3) Evaluation

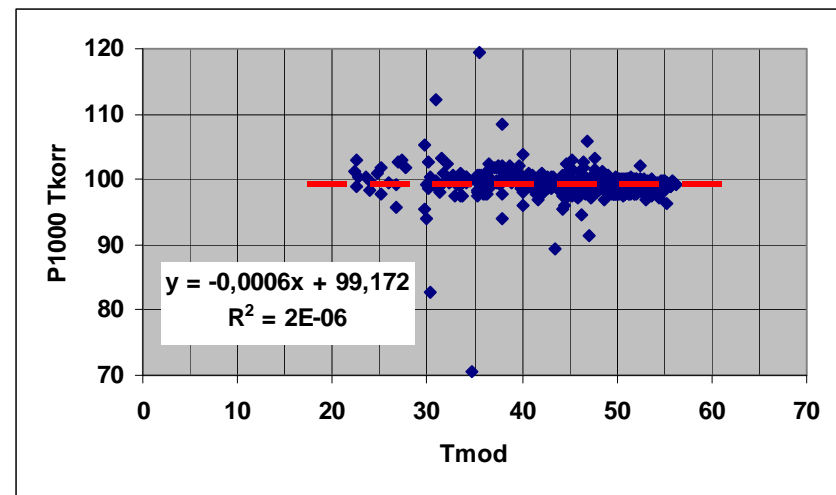
P1000 vs. Tmod

- Determination of Tcoeff. from slope (-0,21 %/K)
- Moderate degree of correlation



P1000 T-corr. vs. Tmod

- STC power 99,2 W
- Deviation by time constants of
 - pyranometer
 - module back temperature

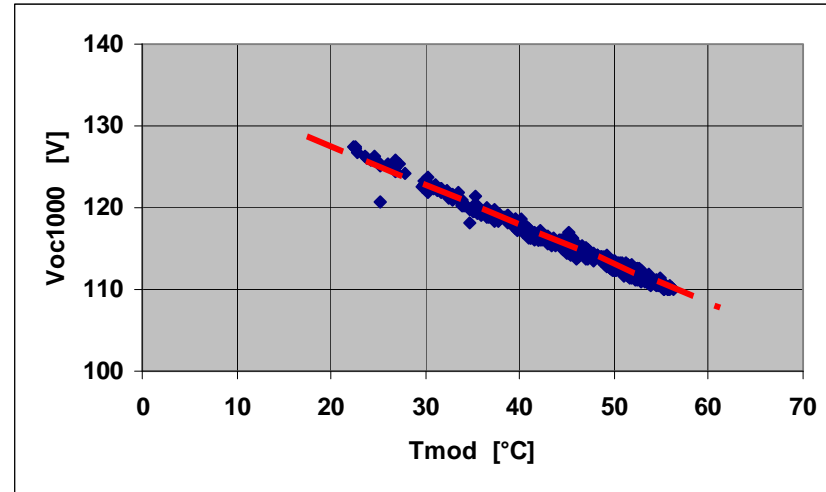


Power and temperature coefficient :

(4) Improvement of accuracy

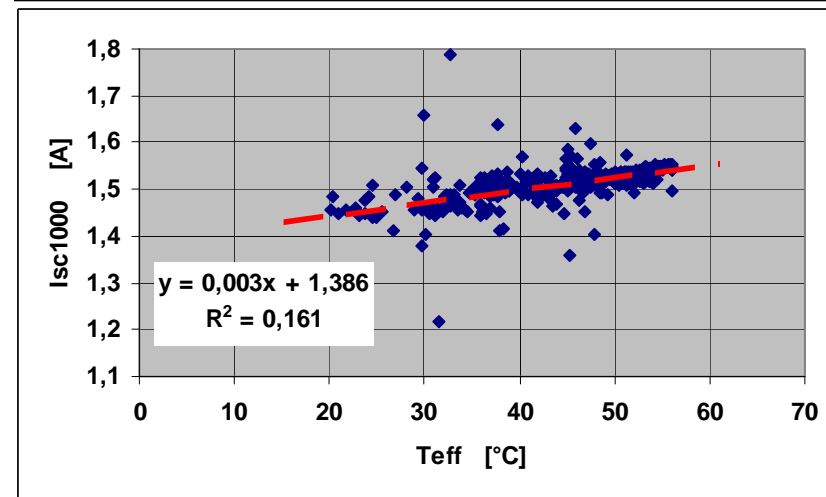
Voc1000 vs. Tmod

- Determination of STC-Voc
- Determination Tcoeff Voc
- Correction of Tmod using Voc1000 → Teff

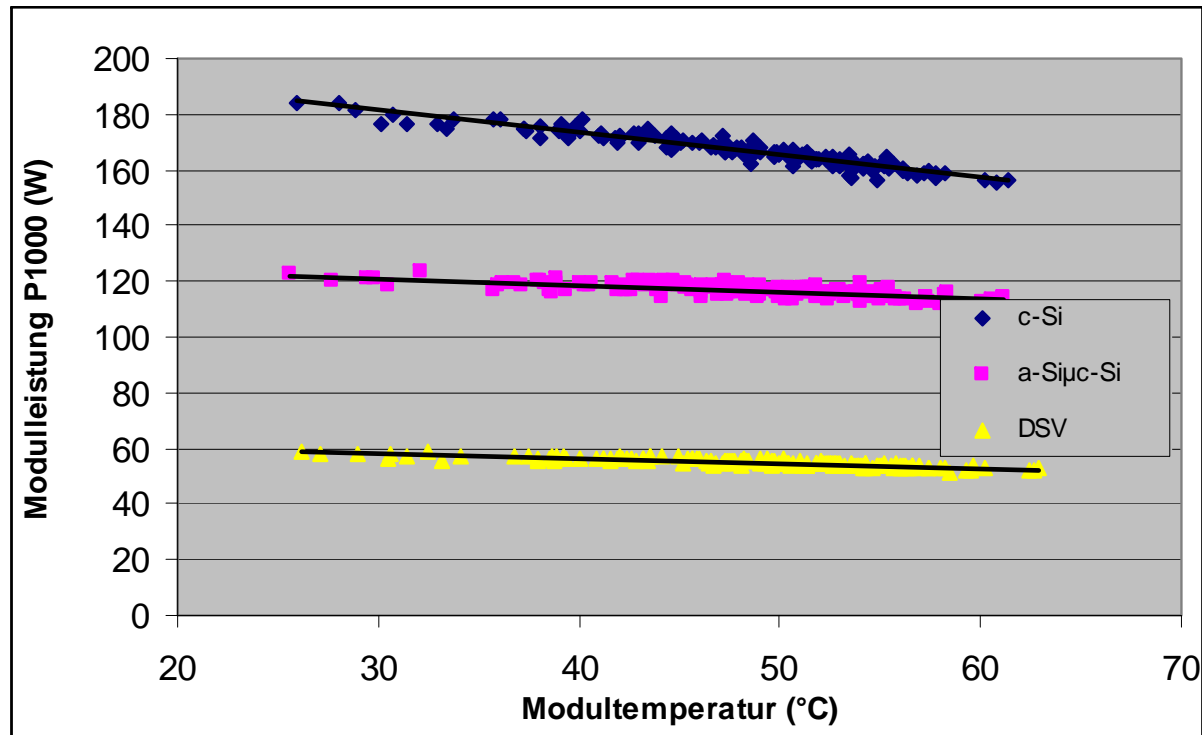


Isc1000 vs. Teff

- Determination of Isc@STC
 - Definition: $E_{eff} = I_{sc} / I_{sc@STC}$
- Module used as irradiance sensor
=> “Self referencing”



Power and temperature coefficient : Example c-Si, a-Si/ μ c-Si, CdTe



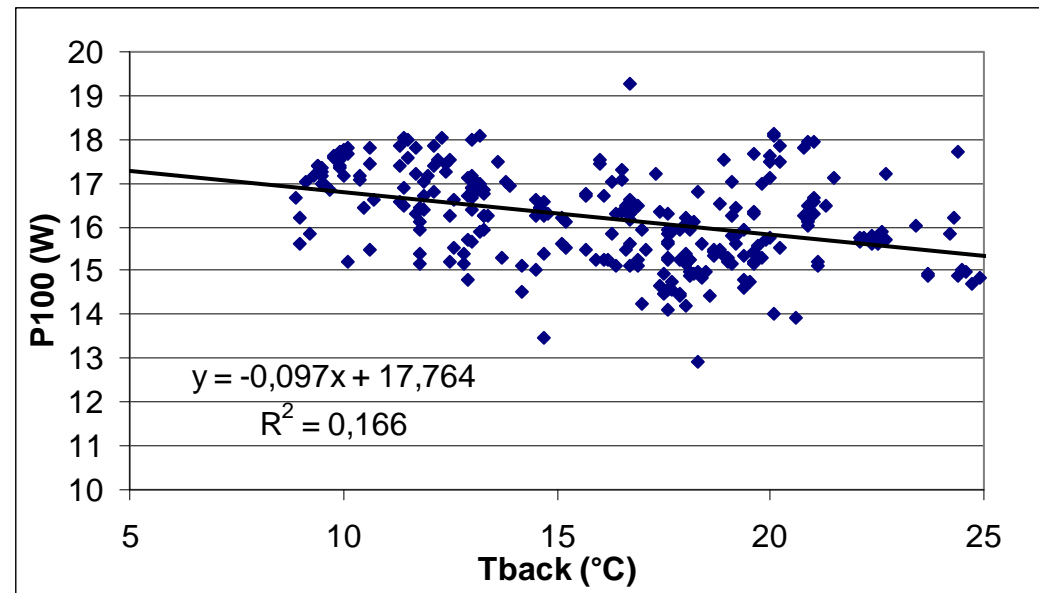
	c-Si	a-Si/ μ c-Si	CdTe
Pmpp @ 25 °C (W)	185.2	122.4	59.1
Tk Pmpp (%/K)	-0.42	-0.2	-0.29

Parameter determination under low irradiance

June 2011, irradiance interval (Pyranometer) (98...102) W/m²

Linear Correction of measured power to 100 W/m²

Plot vs. back temperature



Spectral- and incidence angle influences

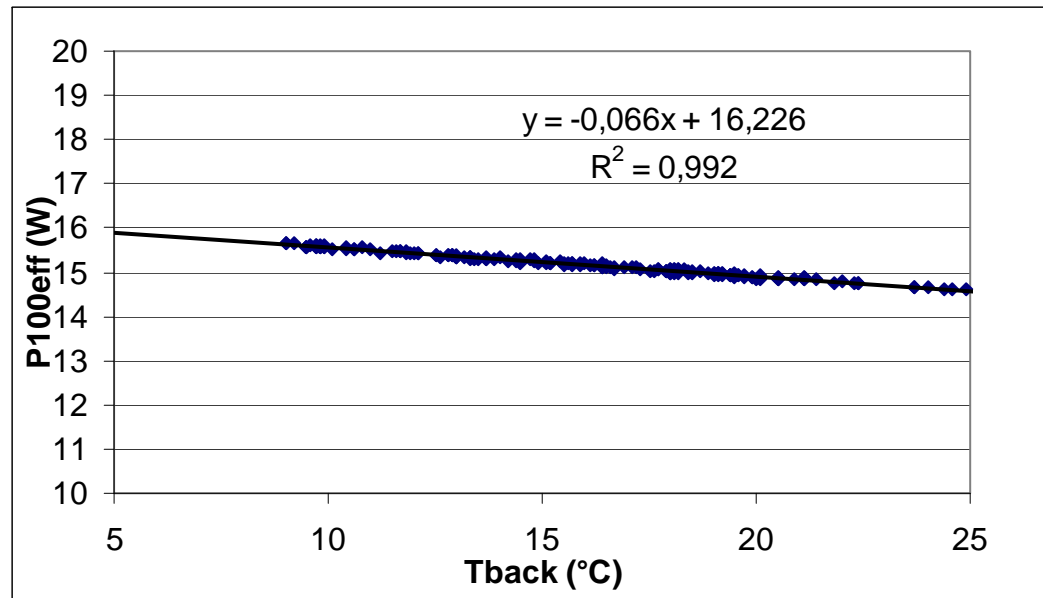
→ No accurate evaluation possible!

Parameter determination under low irradiance

June 2011, Self referencing Eeff = (0.098...0.102) suns

Linear Correction of measured power to 0.1 suns

Plot vs. back temperature



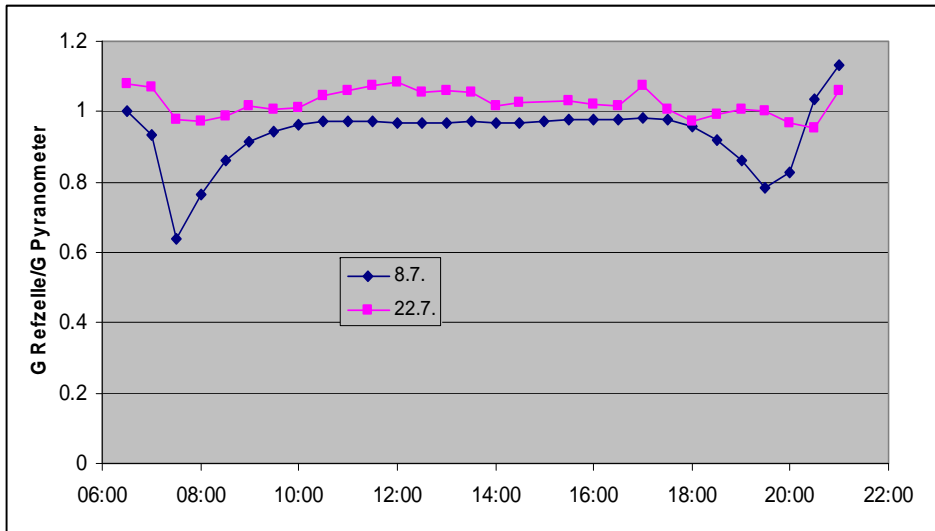
Accurate evaluation possible! → low irradiance degradation

Self referencing of irradiance



ZSW Testfeld Wllderstall

Reference cell or pyranometer?

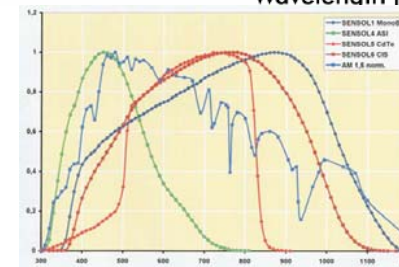
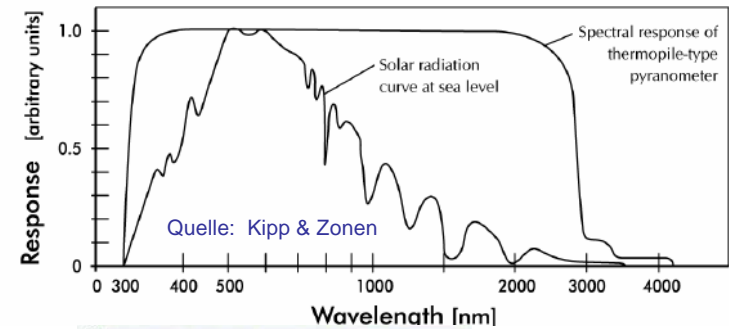


Ratio of c-Si sensor to pyranometer sunny (8.7.) und cloudy (22.7.) day

- Moderate deviation under direct irradiation around noon time and under diffuse light
- strong deviation under direct light morning/evening (incidence angle, spectrum)

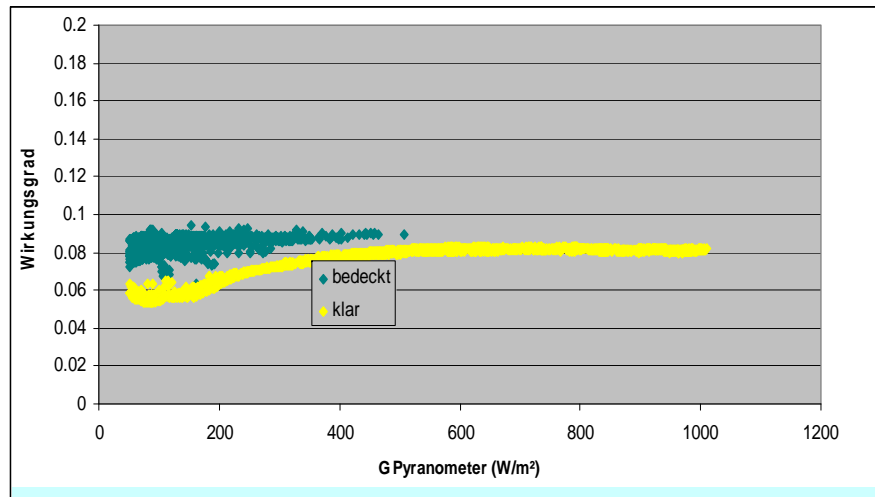


Pyranometer

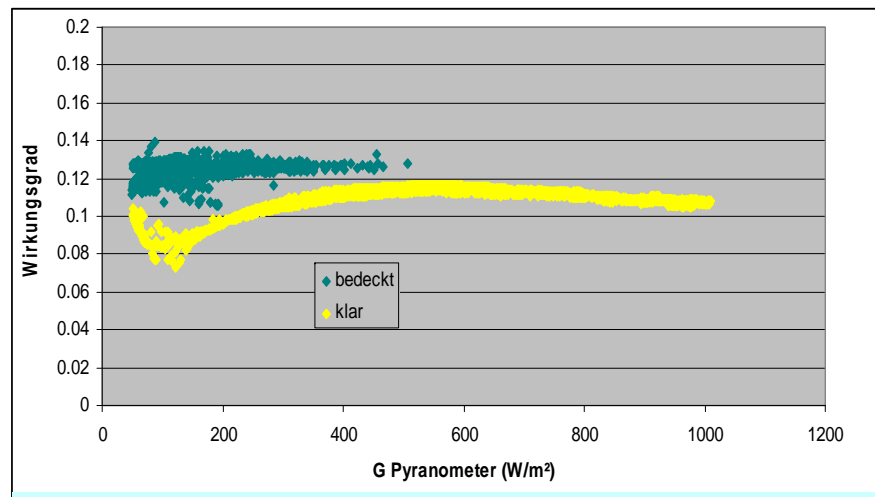


ISET Sensors

Efficiency vs. pyranometer irradiance



a-Si/μc-Si: Efficiency vs. G



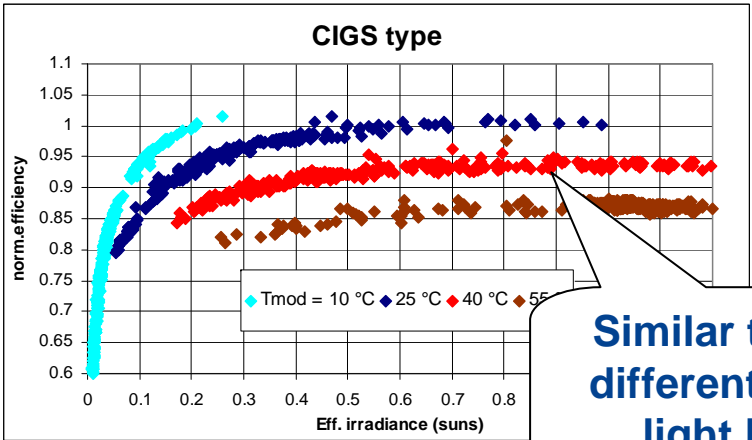
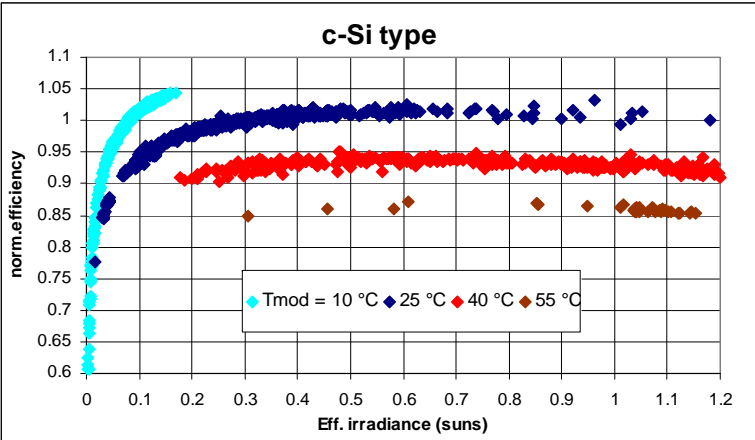
c-Si: Efficiency vs. G

Data are as measured:

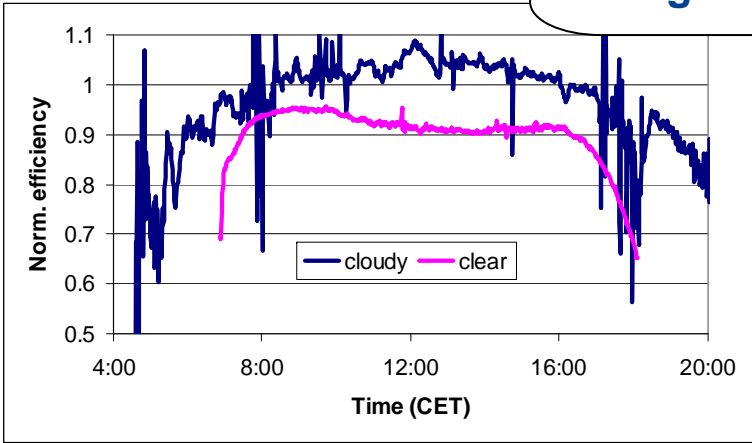
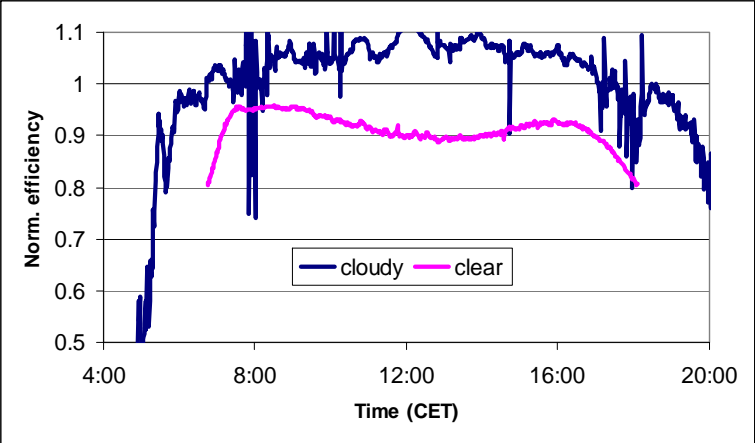
- **Cloudy day:**
high efficiency
- **Sunny day:**
strong influence of spectrum
and incidence angle
morning/evening
Temperature influence at noon
- **NO UNIQUE FUNCTION!**

Efficiency vs. effective irradiance (1)

Normalized efficiency vs. effective irradiance with parameter Tmod (top) and daily profile cloudy/clear (bottom)



Similar to c-Si, different at low light level



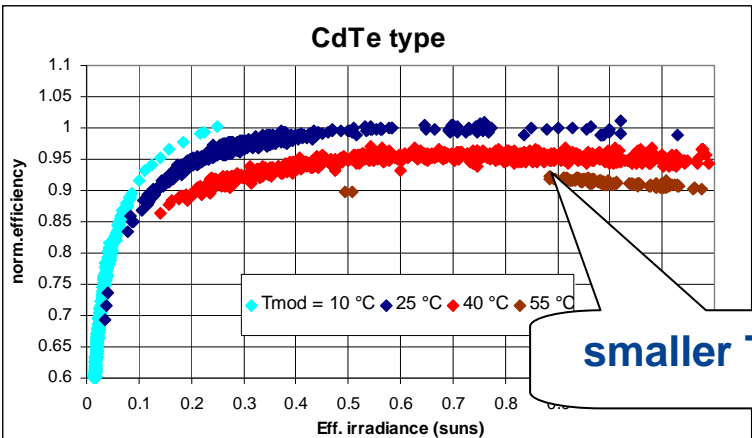
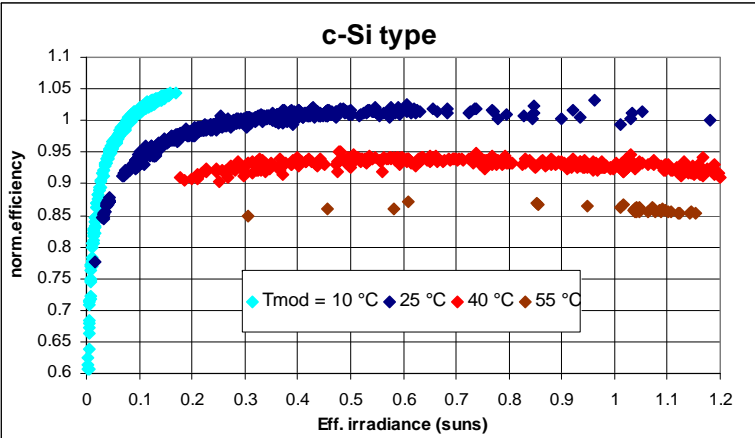
c-Si

CIGS

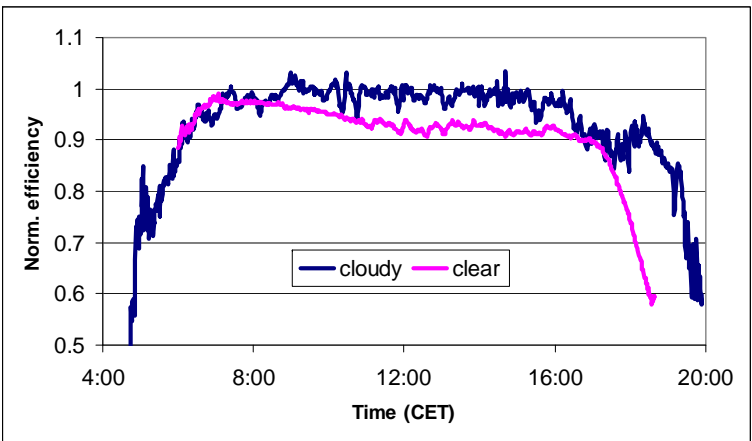
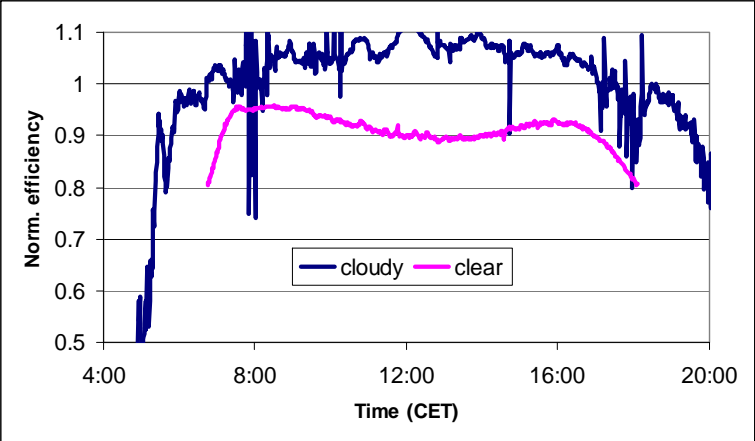


Efficiency vs. effective irradiance (2)

Normalized efficiency vs. effective irradiance and daily profile cloudy/clear

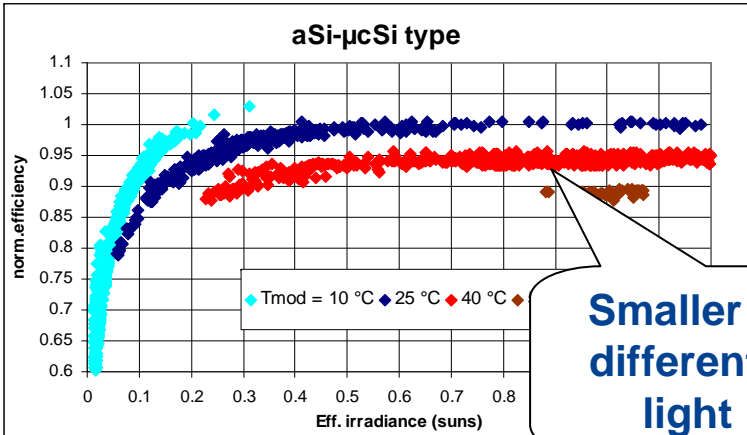
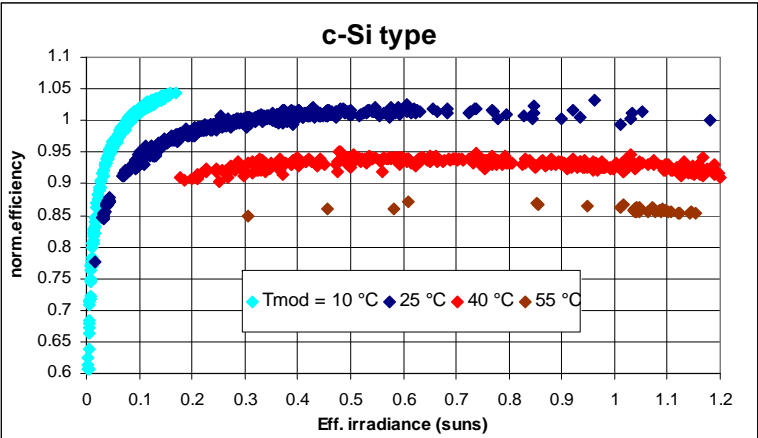


smaller T-coeff.

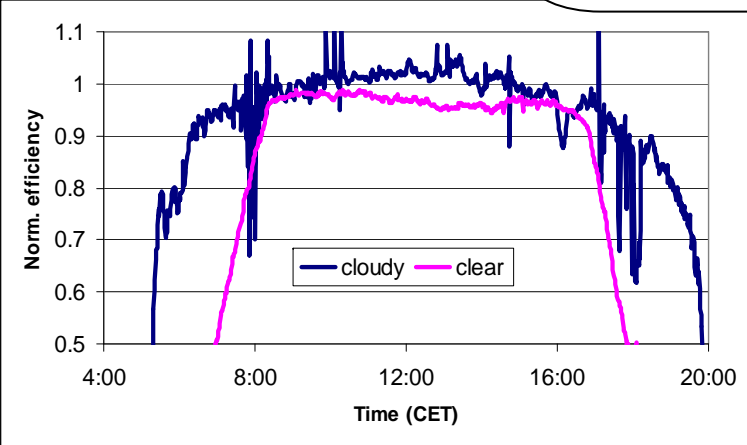
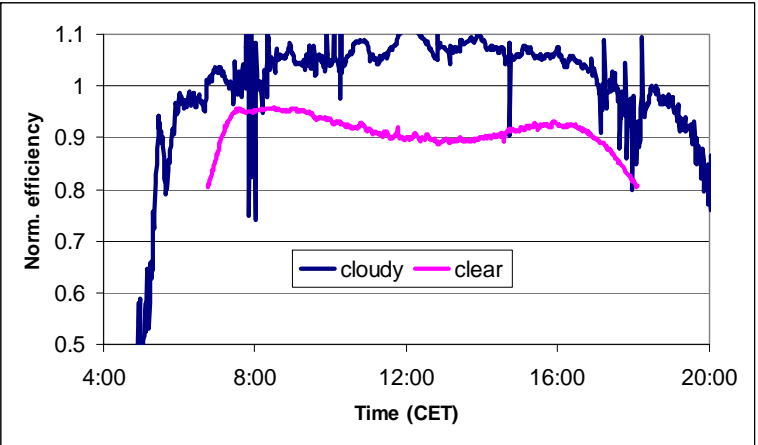


Efficiency vs. effective irradiance (3)

Normalized efficiency vs. effective irradiance and daily profile cloudy/clear



Smaller Tcoeff. different at low light level



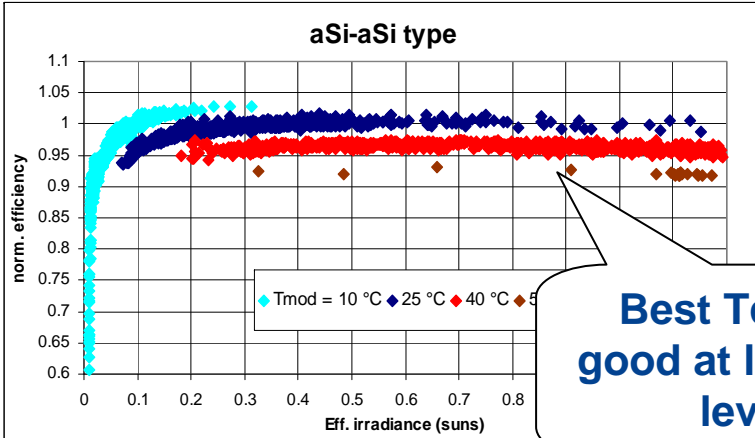
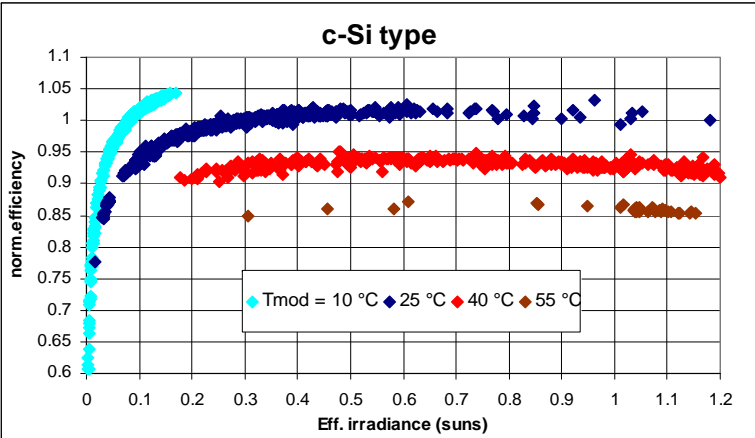
c-Si

a-Si/ μ c-Si

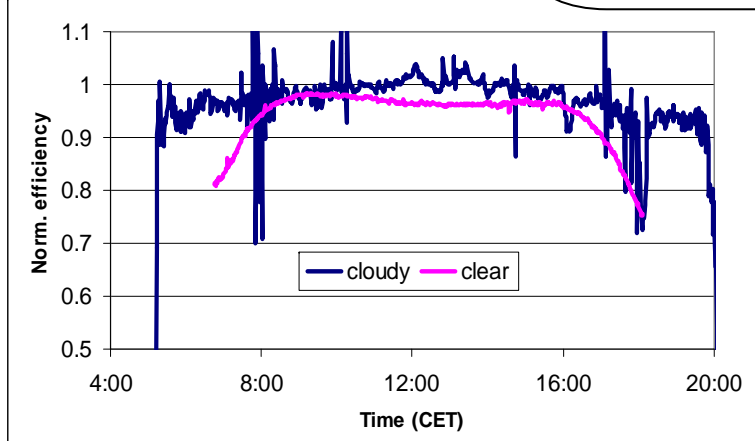
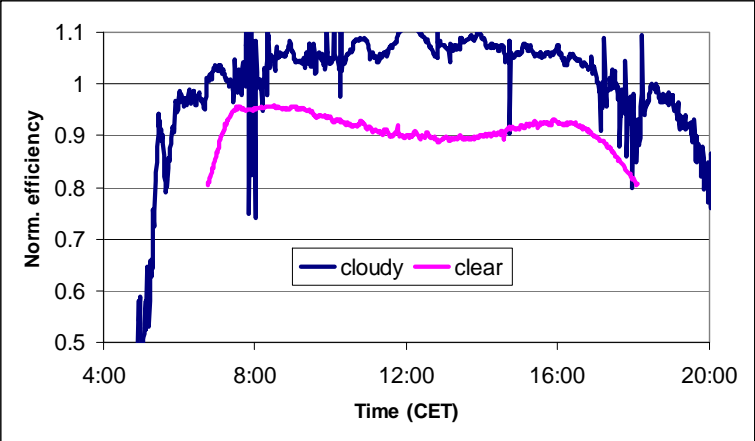


Efficiency v s. effective irradiance(4)

Normalized efficiency vs. effective irradiance and daily profile cloudy/clear



Best Tcoeff., good at low light level



c-Si

a-Si/a-Si

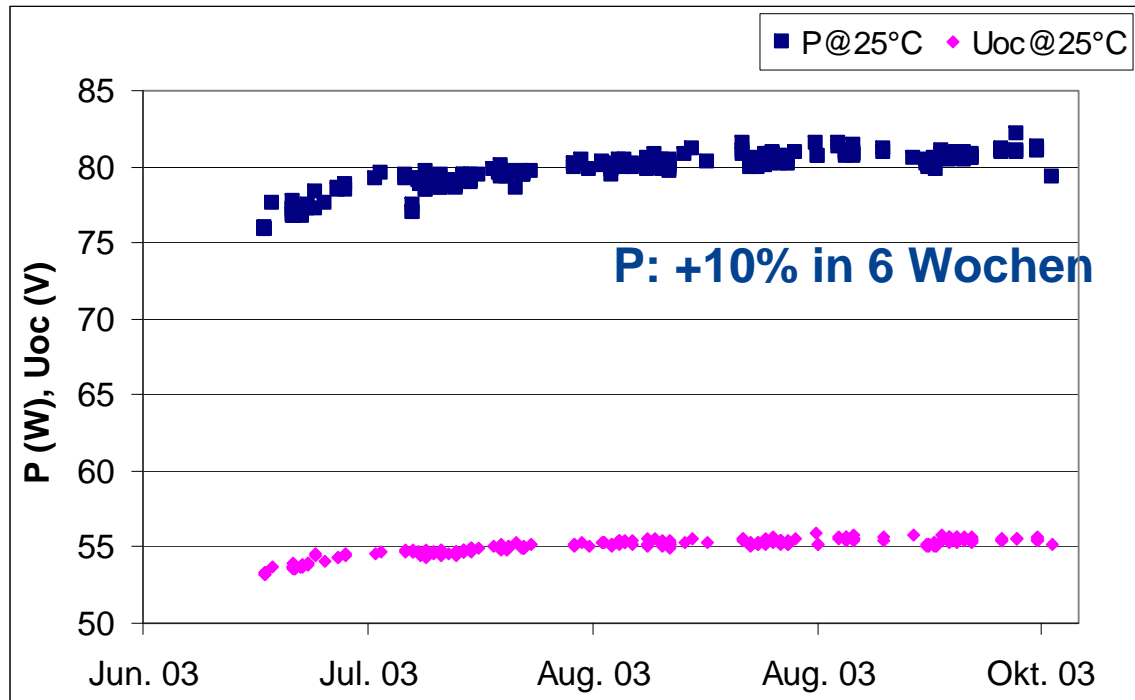


Long term stability

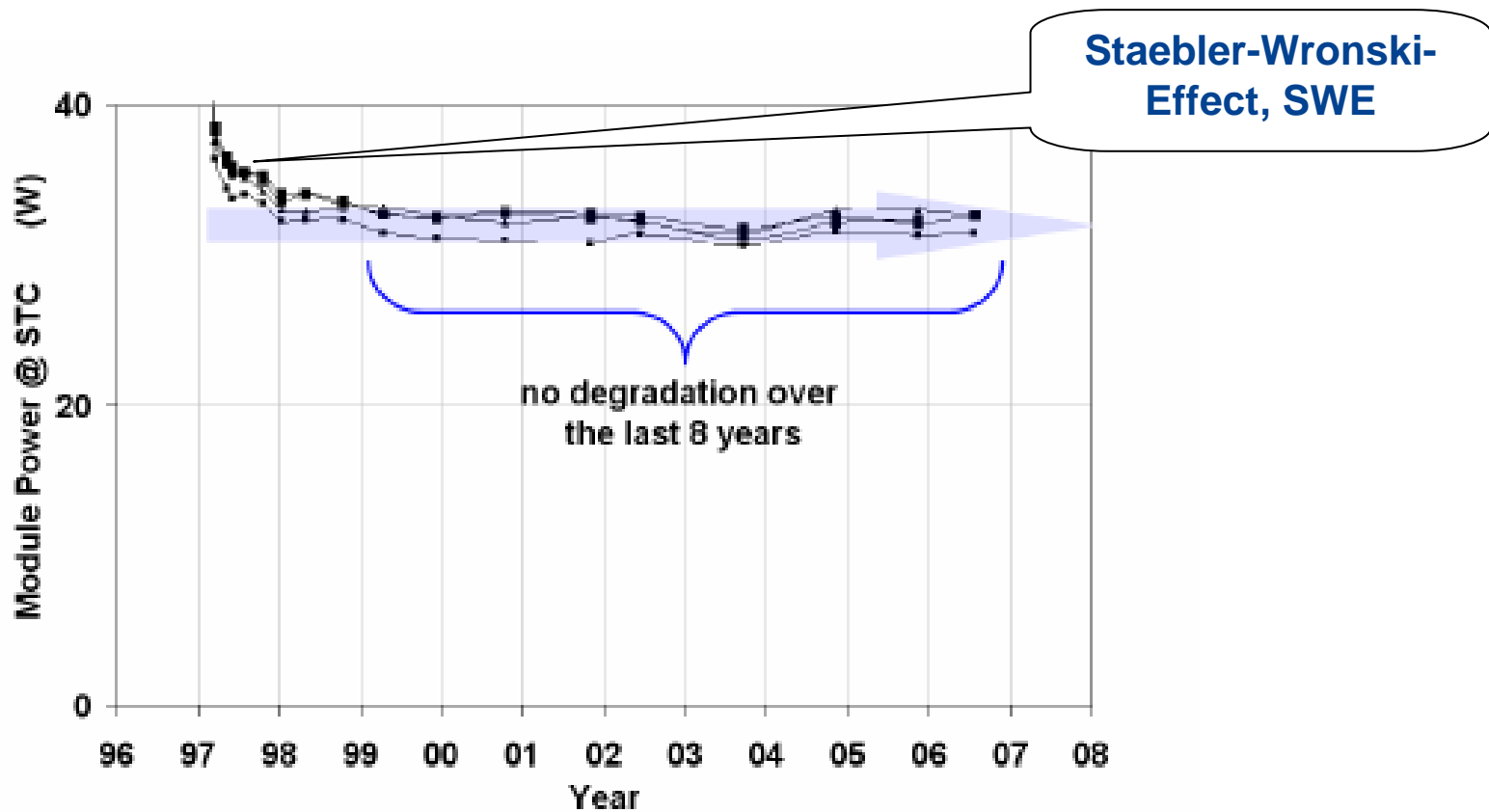


ZSW Test Field Wllderstall

Initial Light-Soaking of CIGS Module

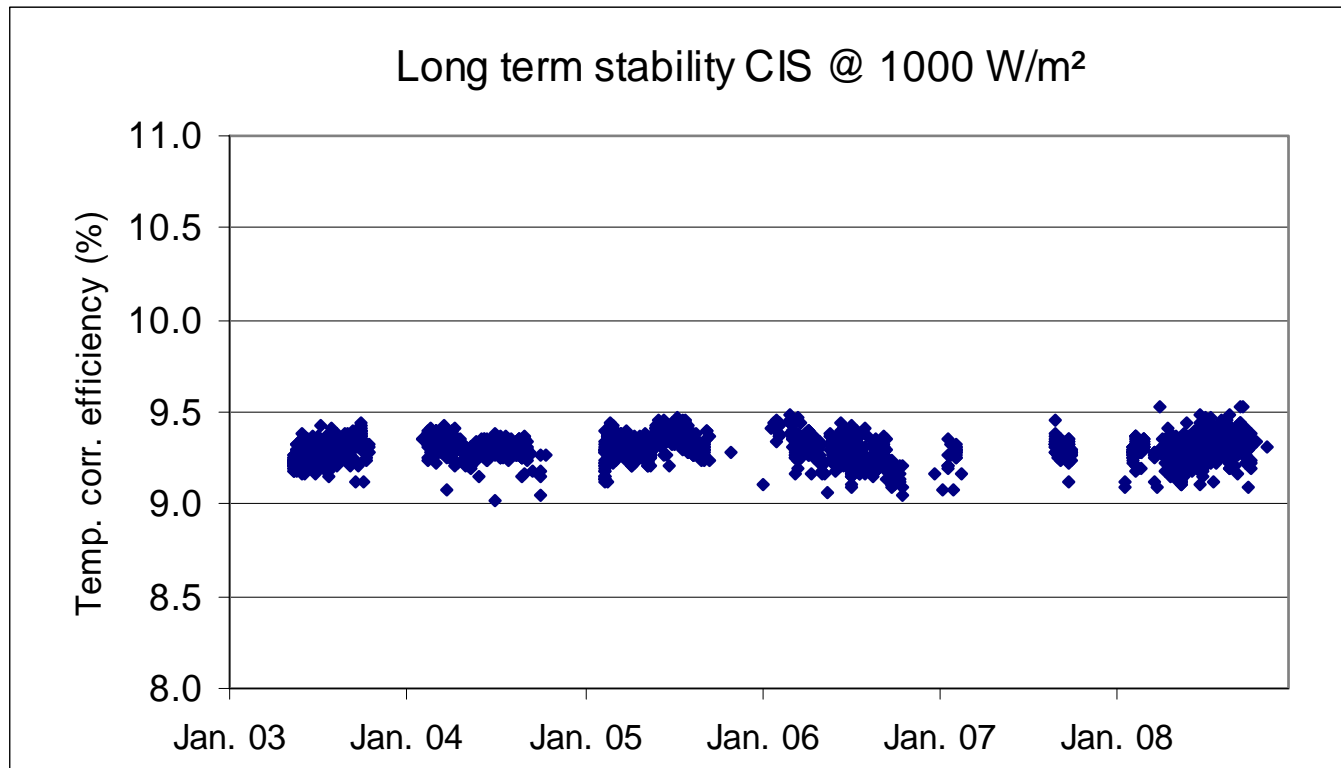


Initial degradation of a-Si/a-Si Modul



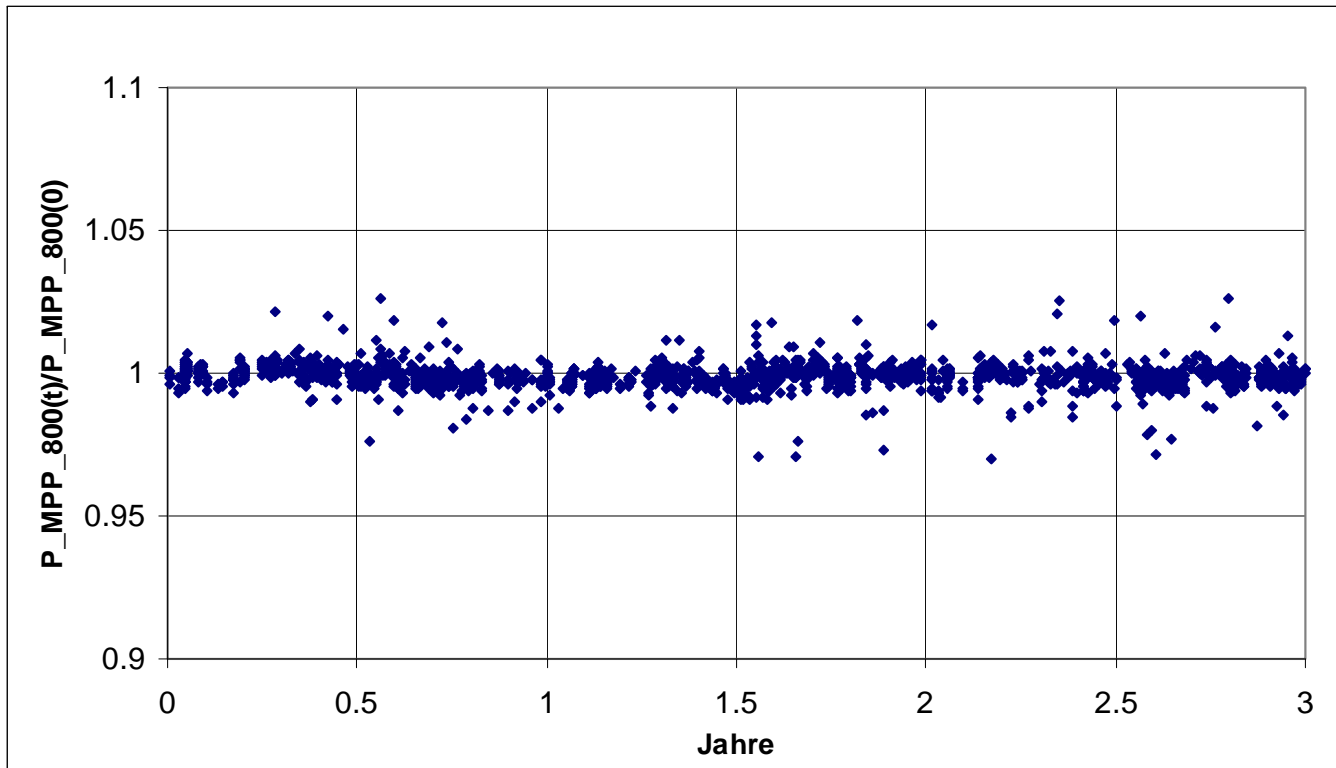
Source: Schott Solar, 21st EU PVSC

Long term stability of CIS Module



Measurement close to AM1.5 and normal incidence, then temperature correction

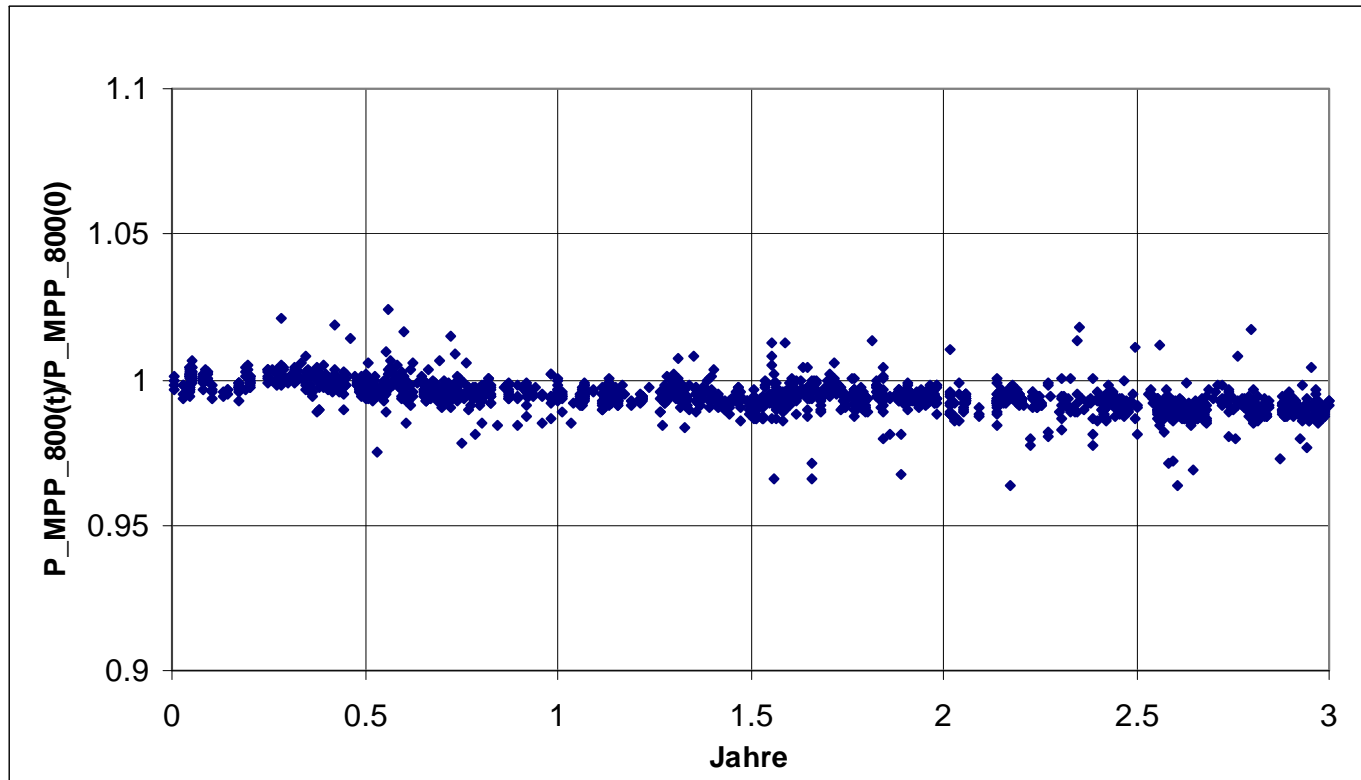
Long term stability of CIGS Module @ 800 W/m²



Continuous evaluation possible

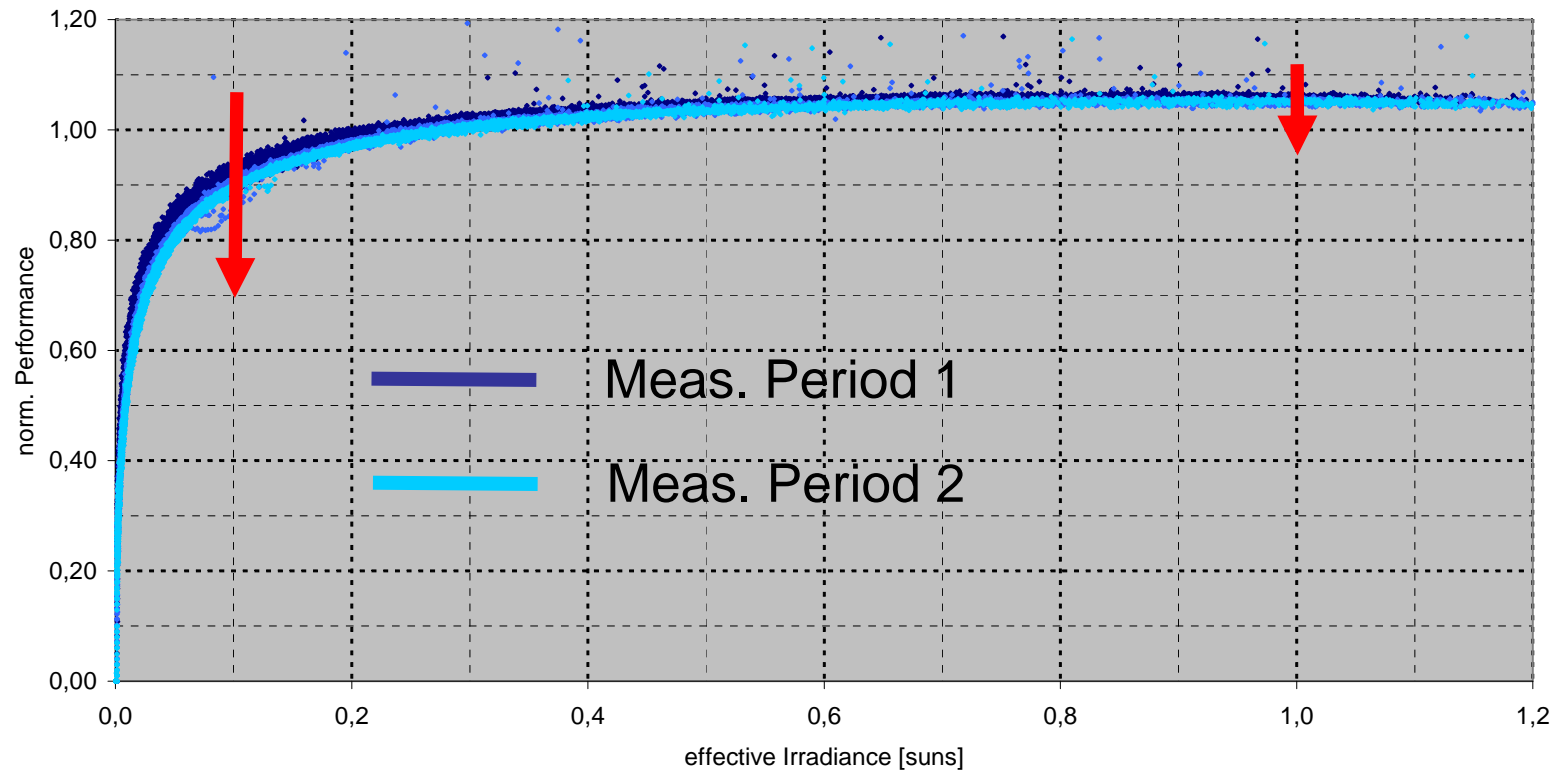


Which degradation rate can be detected?



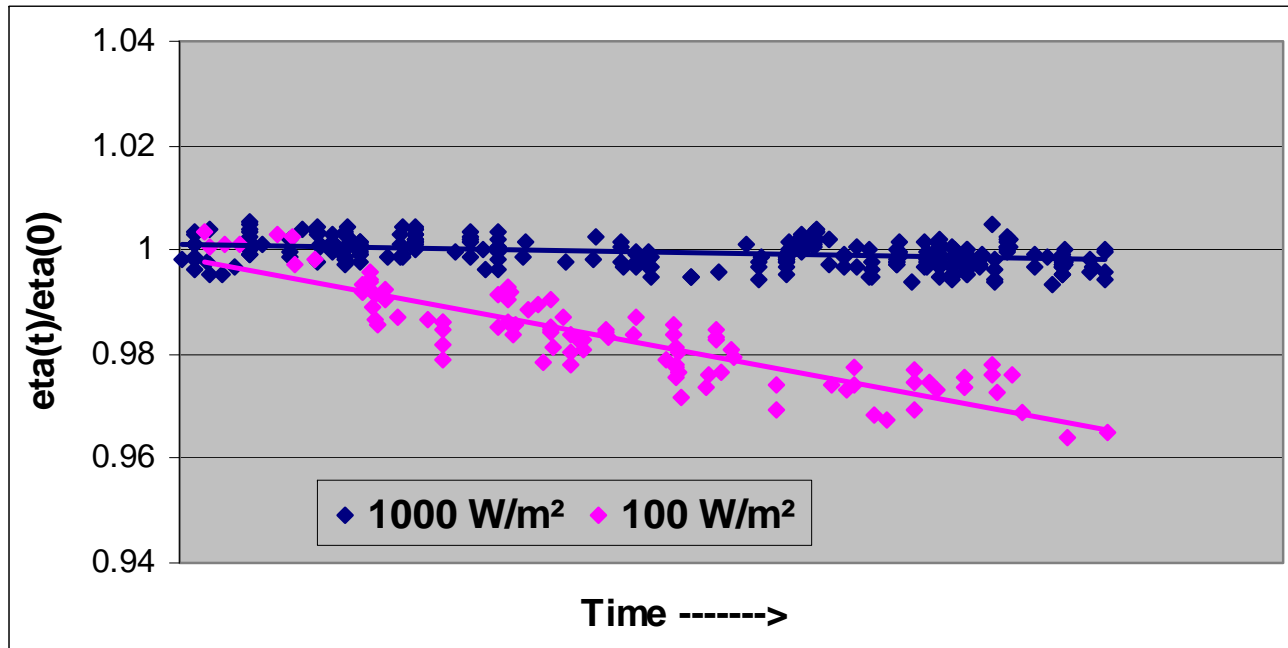
Here assumed 0,3 % per year

Effective efficiency, corrected to reference temperature and normalized to P_{nom}



Low light level degradation / STC-Degradation

Outdoor measurements



Different kinetics

Potential Induced Degradation

(1) Leakage current indoor

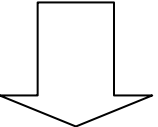
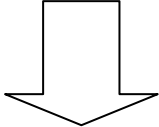
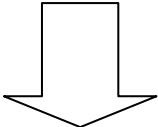
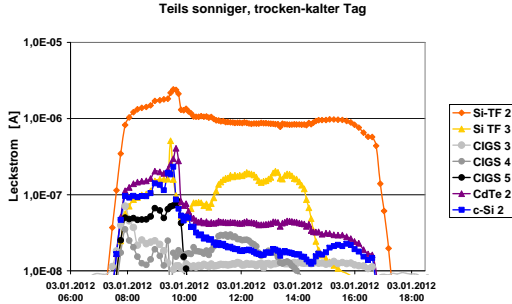
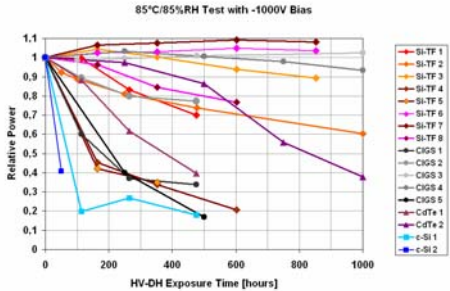
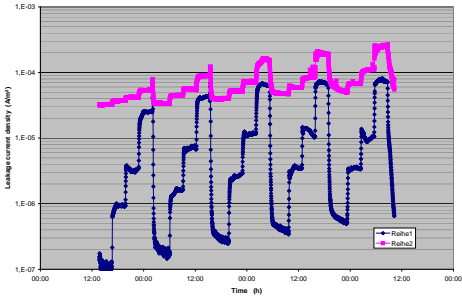
35....85 °C
 50...95 %
 -1000 V
 some hours

(2) Power degrad. indoor

85 °C
 85 %
 -1000 V
 1000 h

(3) Leakage current outdoor

Module temperature
 Humidity
 Generator Voltage
 months to years



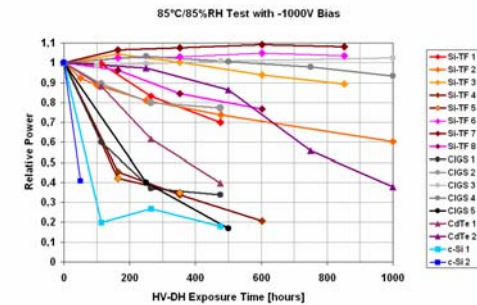
Estimation of Time to PID Failure



Time to PID Failure

Module Type	Q _ HV-DH for P90 [C/m ²]	Daily* Qd from Outdoor [mC/m ²]	Time* to P90 t [a]
c-Si 2	0,6	2	0,8
CIGS 1	1,4	1,6	2,5
Si-TF 2	33	35	2,6
CdTe 2	23	7,8	7,9
Si-TF 6	> 300	1,4	> 5*E2
CIGS 3	> 37	0,19	> 5*E2
CIGS 4	> 87	0,5	> 5*E2

* Average values fall/winter at Widdersall



„PID-Failure“
90 % of initial power (P90)

- Time to PID Failure depends on climate

Summary

- Methods for evaluation of characteristic module parameters from field data have been presented
- Self referencing uses the module itself as a best matched irradiance sensor
- Module power is a unique function of effective irradiance, → transformation to laboratory measurements under reference conditions
- From long term measurements stability trends can be extracted with high accuracy
- Time to PID Failure can be estimated

Thank you for your attention!



ZSW Testfeld Wildderstell